

**AMENDMENTS TO THE SPECIFICATION:**

**Please replace the paragraph at page 3, beginning line 10 and ending on line 23, with the following:**

According to an aspect of the present invention, there is provided a semiconductor device having a MOSFET, the MOSFET comprising source and drain regions formed in a major surface region of a semiconductor substrate, a gate insulating film formed on a channel region between the source and drain regions, a gate electrode which is formed on the gate insulating film and includes formed of a poly-Si<sub>1-x</sub>Ge<sub>x</sub> layer having a Ge/(Si+Ge) composition ratio  $x$  ( $0 < x < 0.2$ ), a first metal silicide film which is formed on the gate electrode and essentially consists of NiSi<sub>1-y</sub>Ge<sub>y</sub>, and second and third metal silicide films which are formed on the source and drain regions, respectively, and essentially consist of NiSi.

**Please delete the paragraph beginning at page 3, line 24 and ending at page 4, line 9.**